Unit in mm

TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N-CHANNEL IGBT

GT15J102

HIGH POWER SWITCHING APPLICATIONS

MOTOR CONTROL APPLICATINS

• High Input Impedance

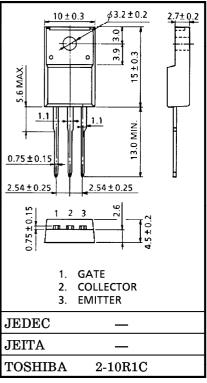
• High Speed : $t_f = 0.35 \mu s$ (Max.)

• Low Saturation Voltage: VCE (sat)=4.0V (Max.)

• Enhancement-Mode

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT	
Collector-Emitter Voltage		VCES	600	V	
Gate-Emitter Voltage		v_{GES}	±20	V	
Collector Current	DC	$I_{\mathbf{C}}$	15	A	
	1ms	I_{CP}	30		
Collector Power Dissipation ($Tc = 25$ °C)		PC	35	w	
Junction Temperature		T_{j}	150	°C	
Storage Temperature Range		$T_{ m stg}$	-55~150	°C	

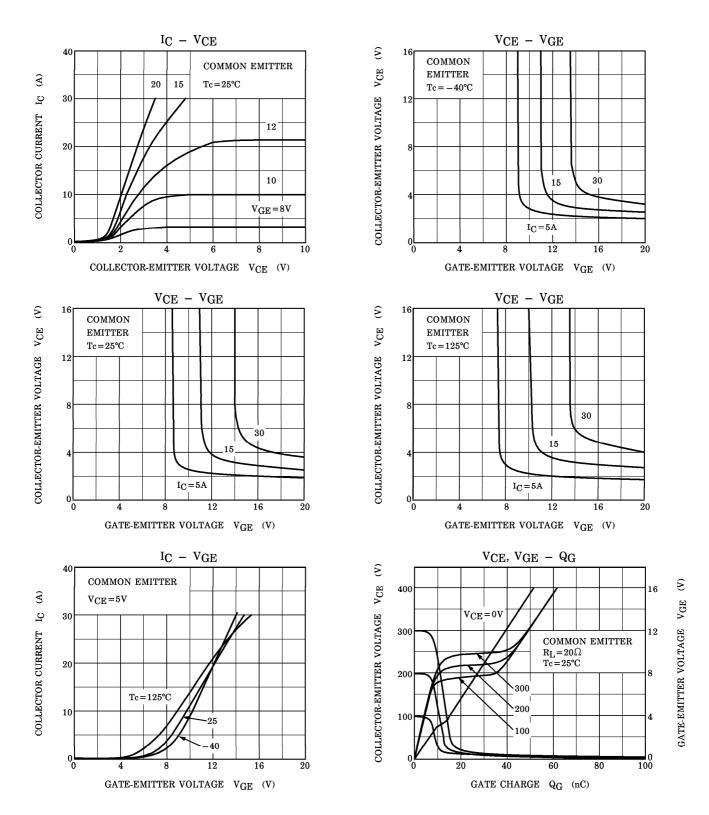


Weight: 1.7g

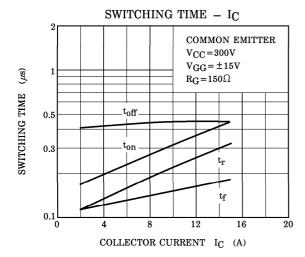
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

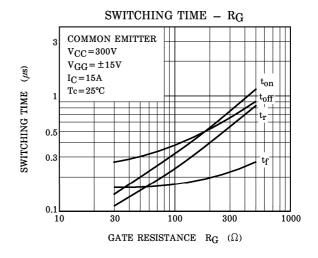
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$	_	_	±500	nA
Collector Cut	-off Current	I_{CES}	$V_{CE} = 600V, V_{GE} = 0$	_	_	1.0	mA
Gate-Emitter	Cut-off Voltage	V _{GE} (OFF)	$I_{\text{C}} = 15 \text{mA}, V_{\text{CE}} = 5 \text{V}$	3.0	_	6.0	V
Collector-Emi Saturation Vo		V _{CE (sat)}	$I_{C} = 15A, V_{GE} = 15V$	_	3.0	4.0	V
Input Capacitance		$\mathrm{c}_{\mathrm{ies}}$	$V_{CE} = 10V, V_{GE} = 0, f = 1MHz$	_	1100	_	pF
Switching Time	Rise Time	t_r	$\begin{array}{c c} V_{\text{OUT}} \\ V_{\text{IN}} \\ \hline \\ 150\Omega \end{array} \begin{array}{c} V_{\text{OUT}} \\ \hline \\ \sim \\ V_{\text{CC}} = 300 \text{V} \end{array}$	_	0.30	0.60	
	Turn-on Time	ton		_	0.40	0.80	
	Fall Time	tf		_	0.15	0.35	μ s
	Turn-off Time	$t_{ m off}$		_	0.50	1.00	

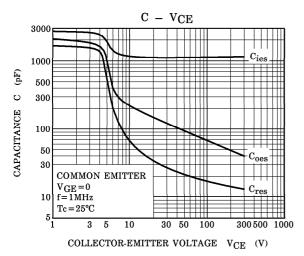
1 2003-03-12

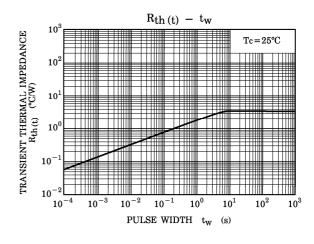


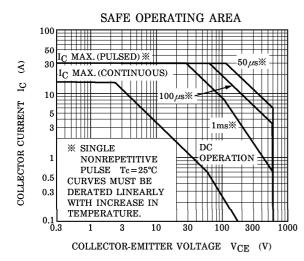
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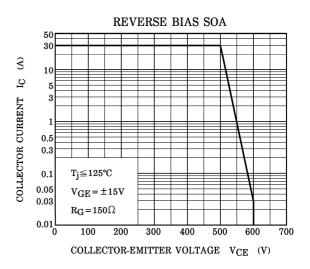












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